TOSHIBA Photocoupler GaAlAs Ired & Photo IC

TLP559(IGM)

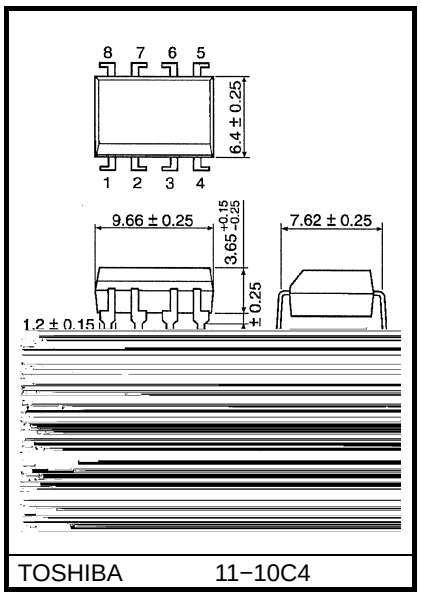
Transistor Inverters

Air Conditioner Inverters

Line Receivers

Intelligent Power Modules (IPMs) Interfaces

Unit: mm



TOSHIBA 11−10C4

Weight: 0.54 g (typ.)

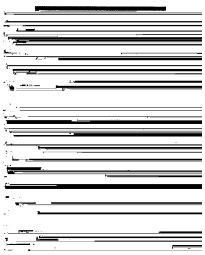
The TOSHIBA TLP559(IGM) consists of a high-output GaAlAs light emitting diode optically coupled to a high-speed photodiode with a transistor amplifier.

The TLP559(IGM) has no internal base connection. The Faraday shield in the photodetector chip provides an effective common-mode noise transient immunity.

The TLP559(IGM) guarantees minimum and maximum propagation delay times, a relative time difference between the rise and fall times, and common-mode transient immunity. Therefore, the TLP559(IGM) is suitable for an isolation interface between an Intelligent Power Module (IPM) and a control IC in motor control applications.

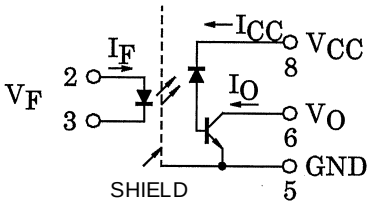
- Isolation Voltage: 2500 Vrms (min)
- Common-Mode Transient Immunity: ±10 kV/μs (min) @V_{CM} = 1500 V
- Switching Time: t_{pHL}, t_{pLH} = 0.1μs (min), = 0.8μs (max) @I_F = 10 mA, V_{CC} = 15 V, R_L = 20 kΤ, Ta = 25°C
- Switching Time Dispersion: 0.7 μs (max)
  (|tpLH−tpHL|)
- TTL Compatible
- UL Recognized: UL1577, File No. E67349

Pin Configuration (Top view)



1: NC
2: Anode
3: Cathode
4: NC
5: Emitter (GND)
6: Collector (Output)
7: NC
8: V_{CC}

Schematic



Absolute Maximum Ratings (Ta = 25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT
LED	Forward Current	(Note 1)	I_F	25	mA
	Pulse Forward Current	(Note 2)	I_{FP}	50	mA
	Peak Transient Forward Current	(Note 3)	I_{FPT}	1	A
	Reverse Voltage		V_R	5	V
	Diode Power Dissipation	(Note 4)	P_D	45	mW
DETECTOR	Output Current		I_O	8	mA
	Peak Output Current		I_{OP}	16	mA
	Output Voltage		V_O	−0.5 to 20	V
	Supply Voltage		V_{CC}	−0.5 to 30	V
	Output Power Dissipation	(Note 5)	P_O	100	mW
Operating Temperature Range			T_{opr}	−55 to 100	°C
Storage Temperature Range			T_{stg}	−55 to 125	°C
Lead Solder Temperature(10s)		(Note 6)	T_{sol}	260	°C
Isolation Voltage(AC,1min.,R.H. 60%,Ta=25°C)		(Note 7)	BV_S	2500	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Derate 0.8mA above 70°C.
(Note 2) 50% duty cycle,1ms pulse width.
Derate 1.6mA/°C above 70°C.
(Note 3) Pulse width PW ≤ 1μs,300pps.
(Note 4) Derate 0.9mW/°C above 70°C.
(Note 5) Derate 2mW/°C above 70°C.
(Note 6) Soldering portion of lead : up to 2mm from the body of the device.
(Note 7) Device considers a two-terminal device : pins1,2,3 and 4 shorted together and pins5,6,7 and 8 shorted together.

Electrical Characteristics (Ta = 25)

	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	I_F = 16 mA	—	1.65	1.85	V
	Forward Voltage Temperature Coefficient	$\Delta V_F / \Delta Ta$	I_F = 16 mA	—	−2	—	mV /°C
	Reverse Current	I_R	V_R = 5 V	—	—	10	μA
	Capacitance between Terminal	CT	V = 0, f = 1 MHz	—	45	—	pF
DETECTOR	High Level Output Current	$I_{OH\ (1)}$	I_F = 0 mA, V_{CC} = V_O = 5.5 V	—	3	500	nA
		$I_{OH\ (2)}$	I_F = 0 mA, V_{CC} = 30 V, V_O = 20 V	—	—	5	μA
		I_{OH}	I_F = 0 mA, V_{CC} = 30 V, V_O = 20 V, Ta = 70°C	—	—	50	
	High Level Supply Voltage	I_{CCH}	I_F = 0 mA, V_{CC} = 30 V	—	0.01	1	μA
	Supply Voltage	V_{CC}	I_{CC} = 0.01 mA	30	—	—	V
	Output Voltage	V_O	I_O = 0.5 mA	20	—	—	V

Coupled Electrical Characteristics (Ta = 25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_O / I_F	I_F = 10 mA, V_{CC} = 4.5 V, V_O = 0.4 V	25	35	75	%
		I_F = 10 mA, V_{CC} = 4.5 V, V_O = 0.4 V, Ta = −25 to 100°C	15	—	—	
Low Level Output Voltage	V_{OL}	I_F = 16 mA, V_{CC} = 4.5 V, I_O = 2.4 mA	—	—	0.4	V

Isolation Characteristics (Ta = 25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance Input to Output	CS	V = 0, f = 1 MHz (Note 7)	—	0.8	—	pF
Isolation Resistance	R_S	R.H. Ω60%, V_S = 500 V (Note 7)	5×10^{10}	10^{14}	—	T
Isolation Voltage	BV_S	AC , 1minute	2500	—	—	Vrms
		AC , 1second, in oil	—	5000	—	
		DC , 1minute,in oil	—	5000	—	Vdc

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